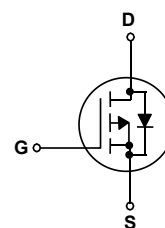
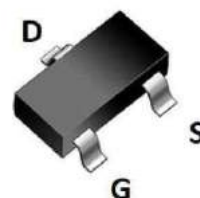


Features

- P-Channel
- Low Gate Charge
- High Power and current handing capability
- Lead free product is acquired

V_{DS}	-12	V
$R_{DS(on),TYP@ V_{GS}=-4.5 V}$	13	m Ω
$R_{DS(on),TYP@ V_{GS}=-2.5 V}$	19	m Ω
I_D	-8	A

SOT-23


Part ID	Package Type	Marking	Packing
ZT1209	SOT-23	1209	3000pcs/Reel

Symbol	Parameter	Rating	Unit	
Common Ratings (T_c=25°C Unless Otherwise Noted)				
V_{GS}	Gate-Source Voltage	±12	V	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-12	V	
T_J	Maximum Junction Temperature	150	°C	
T_{STG}	Storage Temperature Range	-55 to 150	°C	
I_{DM}	Drain Current-Continuous@ Current-Pulsed (Note 1)	$T_C=25^\circ C$ -32	A	
Mounted on Large Heat Sink				
I_D	Drain Current-Continuous	$T_C=25^\circ C$	-8	A
		$T_C=100^\circ C$	-5	A
P_D	Maximum Power Dissipation	$T_C=25^\circ C$	3	W
		$T_C=100^\circ C$	1.25	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	40	°C/W	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J=25°C (unless otherwise stated)						
V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-12	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-12V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±10V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.5	-0.7	-1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-5A	--	13	17	mΩ
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-2.5V, I _D =-4A	--	19	26	mΩ
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-5A	--	14	--	S
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated) (Note 2)						
C _{iss}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	--	1448	--	pF
C _{oss}	Output Capacitance		--	322	--	pF
C _{rss}	Reverse Transfer Capacitance		--	282	--	pF
Q _g	Total Gate Charge	V _{DS} =-10V, I _D =-5A, V _{GS} =-4.5V	--	16	--	nC
Q _{gs}	Gate-Source Charge		--	3.4	--	nC
Q _{gd}	Gate-Drain Charge		--	4.1	--	nC
Switching Characteristics						
T _{d(on)}	Turn-on Delay Time	V _{DS} =-10V, R _L =2Ω, R _G =3Ω, V _{GS} =-4.5V	--	16	--	ns
T _r	Turn-on Rise Time		--	64	--	ns
T _{d(off)}	Turn-Off Delay Time		--	71	--	ns
T _f	Turn-Off Fall Time		--	62	--	ns
Source- Drain Diode Characteristics @ T_J = 25°C (unless otherwise stated)						
I _{SD}	Source-Drain Current (Body Diode)		--	--	-8	A
V _{SD}	Forward on voltage (Note 1)	I _S =-5.0A, V _{GS} =0V	--	--	-1.2	V

Notes:

1.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

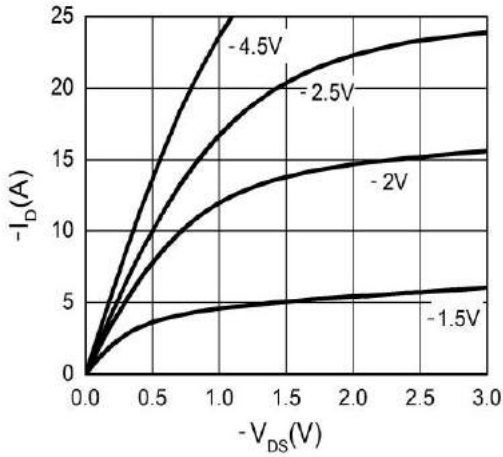


Figure 1. Output Characteristics

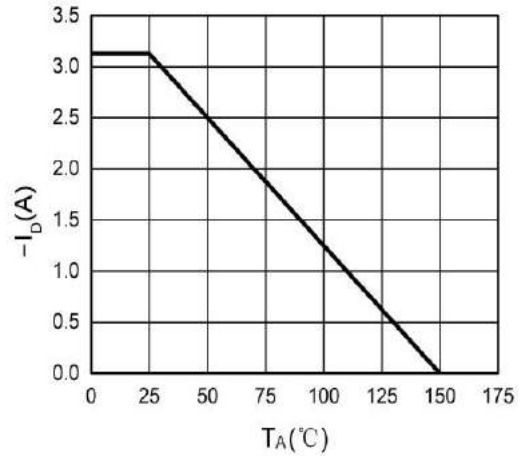


Figure 4. Power Dissipation

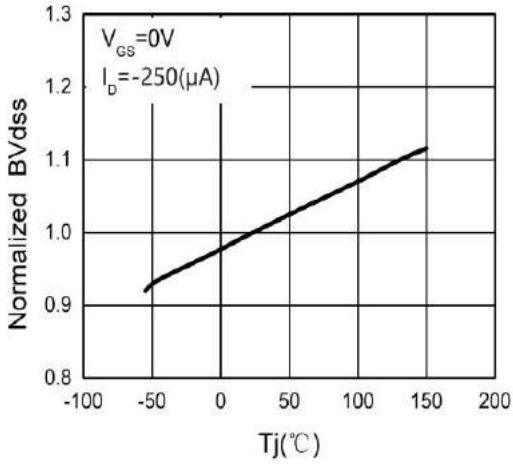


Figure 2. BV_{DS} vs Junction Temperature

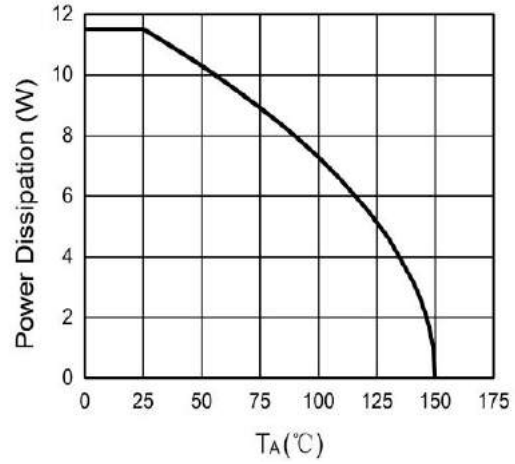


Figure 5. Drain Current

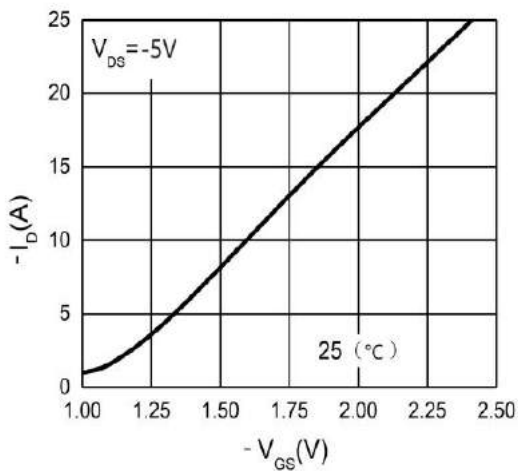


Figure 3. Transfer Characteristics

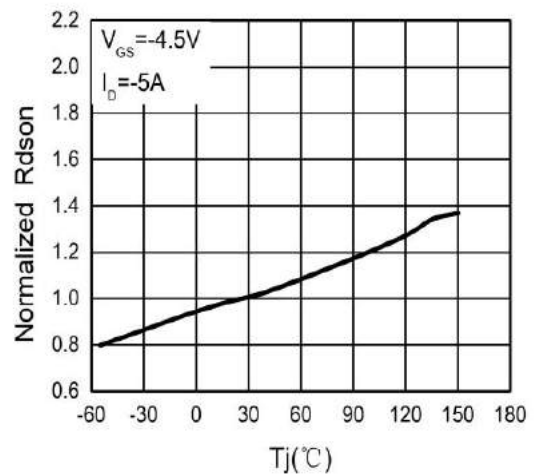


Figure 6. $R_{DS(on)}$ vs Junction Temperature

Typical Electrical And Thermal Characteristics (Curves)

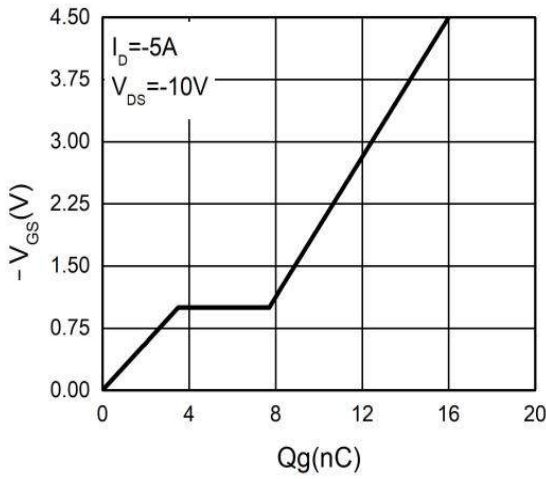


Figure 7. Gate Charge Waveforms

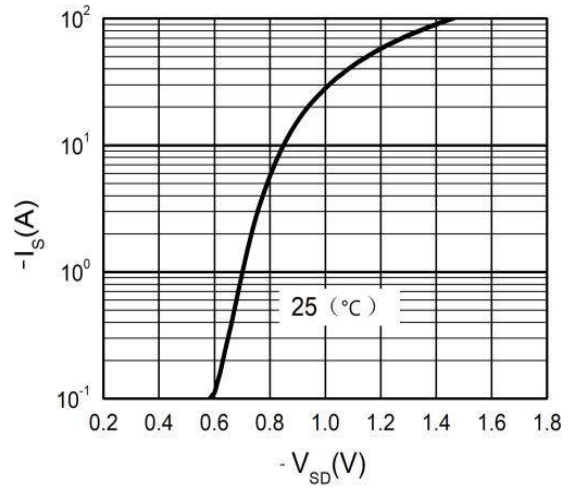


Figure 9. Body-Diode Characteristics

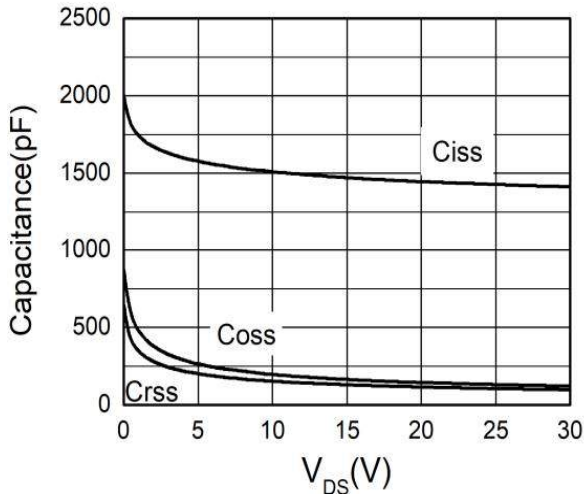


Figure 8. Capacitance

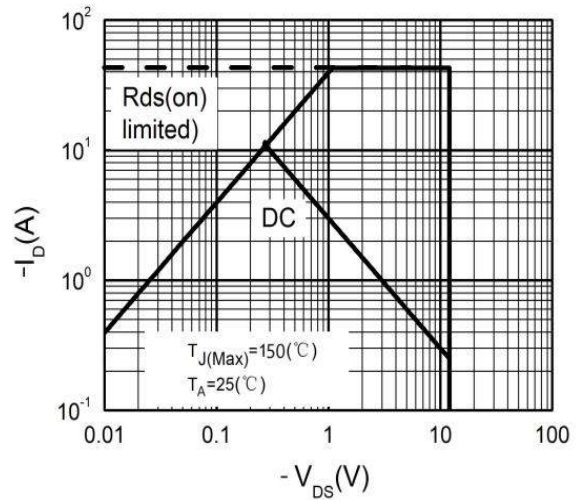
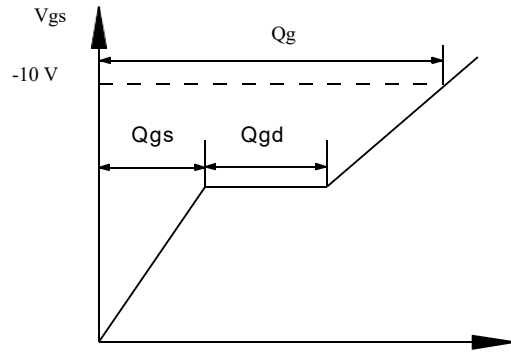
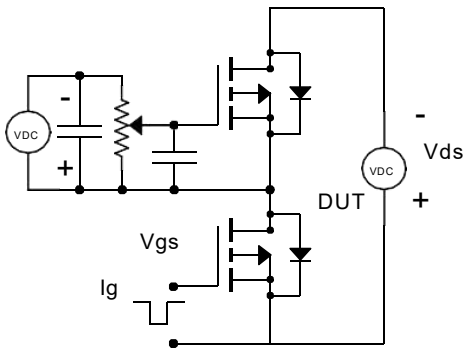
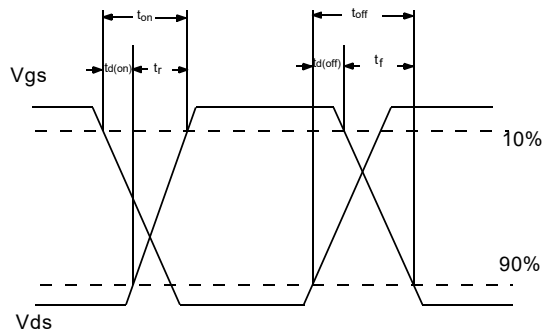
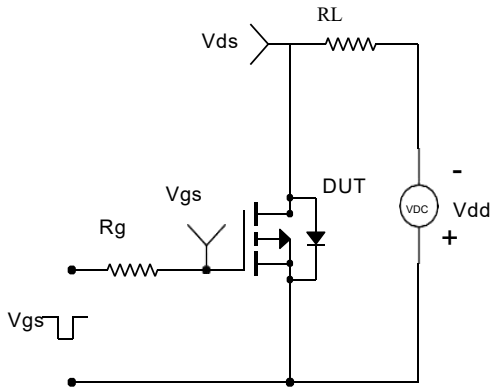


Figure 10. Maximum Safe Operating Area

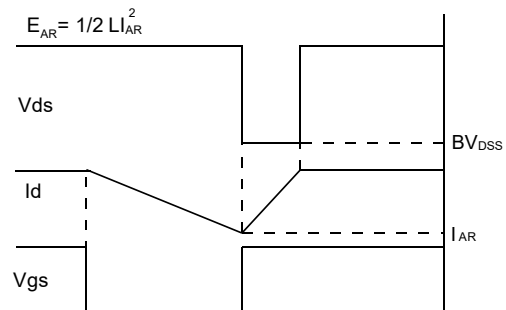
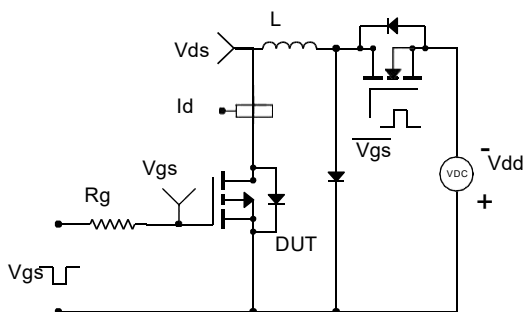
Gate Charge Test Circuit & Waveform



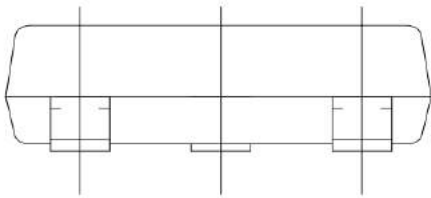
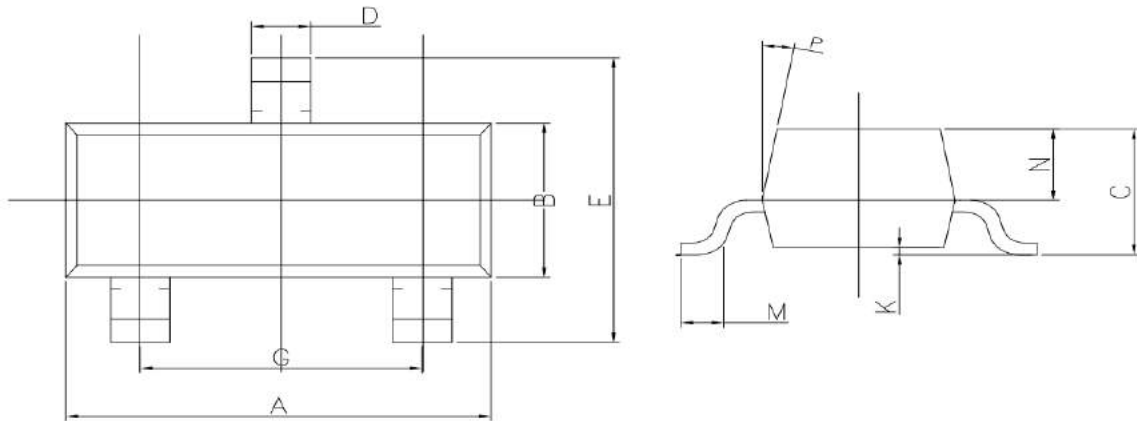
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms



SOT-23 Package Information



DIM	MILLIMETERS
A	2.90 ± 0.1
B	1.30 ± 0.10
C	0.90 ~ 1.15
D	0.40 ± 0.1
E	2.40 ± 0.15
G	1.90 ± 0.10
K	0.00~0.10
M	0.30MIN
N	0.60 ± 0.10
P	10°TYP

Customer Service

Sales and Service:

zj@ztasemi.com